

#### 30V N-Channel Enhancement Mode MOSFET

Voltage 30 V Current 300mA

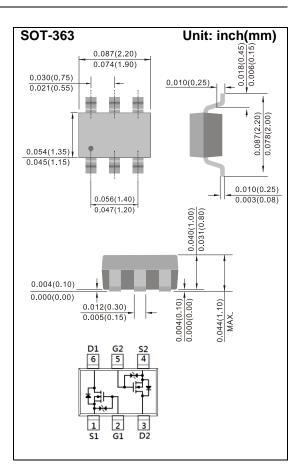
#### **Features**

- Advanced Trench Process Technology
- ESD Protected
- Specially Designed for Relay driver, Speed line drive, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. . (Halogen Free)

#### **Mechanical Data**

• Case: SOT-363 Package

• Terminals : Solderable per MIL-STD-750, Method 2026



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		V <sub>G</sub> s	<u>+</u> 10	V
Continuous Drain Current		ID	300	mA
Pulsed Drain Current		I <sub>DM</sub>	600	mA
Power Dissipation	T <sub>A</sub> =25°C	<b>D</b>	350	mW
	Derate above 25°C	P <sub>D</sub>	2.8	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal Resistance - Junction to Ambient (Note 3)		Reja	357	°C/W



# **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA 30		-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.4	0.75	1.0	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V,I <sub>D</sub> =300mA	-	0.7	1.2	Ω	
		V <sub>GS</sub> =2.5V,I <sub>D</sub> =200mA	-	0.8	1.6		
		V <sub>GS</sub> =1.8V,I <sub>D</sub> =100mA	-	0.9	2.0		
		V <sub>GS</sub> =1.5V,I <sub>D</sub> =50mA	-	1.1	3.0		
		V <sub>GS</sub> =1.2V,I <sub>D</sub> =20mA	-	1.5	4.0		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =24V,V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 8V,V <sub>DS</sub> =0V	-	-	<u>+</u> 10	uA	
Dynamic (Note 4)							
Total Gate Charge	$Q_g$	., ,.,,	-	0.9	-	nC	
Gate-Source Charge	$Q_gs$	V <sub>DS</sub> =10V, I <sub>D</sub> =300mA,	-	0.3	-		
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =4.5V	-	0.2	-		
Input Capacitance	Ciss	\/ 40\/ \/ 0\/	-	45	-	pF	
Output Capacitance	Coss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,	-	14	-		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	0.8	-		
Turn-On Delay Time	td <sub>(on)</sub>	\/ 40\/ L 000 ·· A	-	8.3	-	ns	
Turn-On Rise Time	tr	V <sub>DD</sub> =10V, I <sub>D</sub> =300mA,	-	5.7	-		
Turn-Off Delay Time	td <sub>(off)</sub>	$V_{GS}=4V$ , $R_{G}=10\Omega$ (Note 1,2)	-	35	-		
Turn-Off Fall Time	tf	NG=1012 (1000 1,2)	-	12	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	Is		_		300	mA	
Diode Forward Current	15		_	_	300	111/4	
Diode Forward Voltage	$V_{\text{SD}}$	Is=300mA, V <sub>GS</sub> =0V	-	0.9	1.3	V	

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper
- 4. Guaranteed by design, not subject to production testing.



#### **TYPICAL CHARACTERISTIC CURVES**

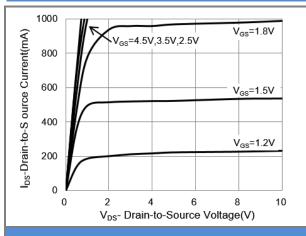


Fig.1 On-Region Characteristics

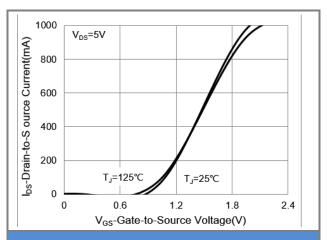


Fig.2 Transfer Characteristics

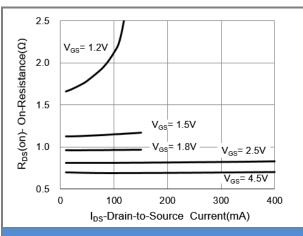


Fig.3 On-Resistance vs. Drain Current

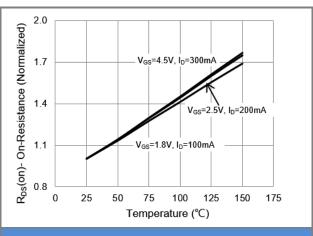


Fig.4 On-Resistance vs. Junction temperature

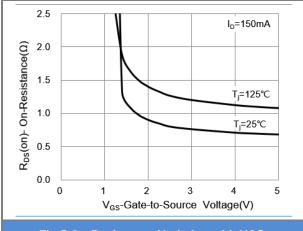
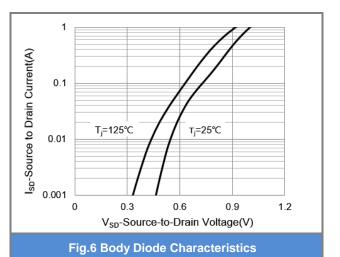


Fig.5 On-Resistance Variation with VGS.





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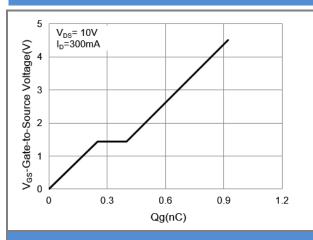


Fig.7 Gate-Charge Characteristics

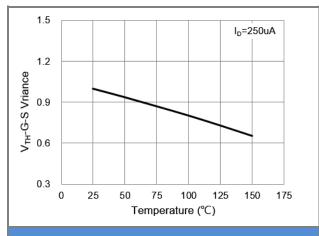


Fig.9 Threshold Voltage Variation with Temperature.

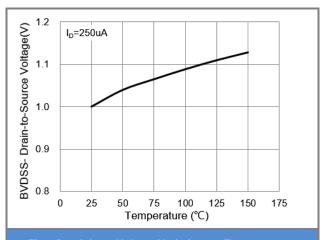


Fig.8 Breakdown Voltage Variation vs. Temperature

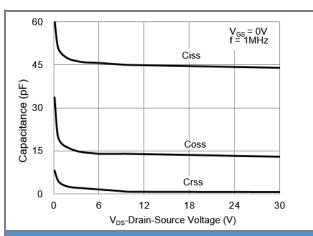


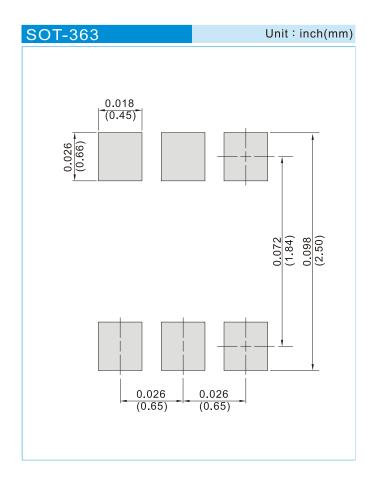
Fig.10 Capacitance vs. Drain-Source Voltage.



# **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking	
PJT7828	SOT-363	3K pcs / 7" reel	T28	
PJT7828	SOT-363	10K pcs / 13" reel	T28	

### **Mounting Pad Layout**





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